

General Description

The WSF3013 is the highest performance trench N-ch and P-ch MOSFETs with extreme high cell density, which provide excellent RDSON and gate charge for most of the synchronous buck converter applications.

The WSF3013 meet the RoHS and Green Product requirement 100% EAS guaranteed with full function reliability approved.

Features

- Advanced high cell density Trench technology
- Super Low Gate Charge
- Excellent CdV/dt effect decline
- 100% EAS Guaranteed
- Green Device Available

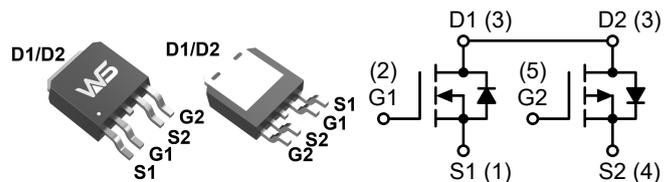
Product Summary

BVDSS	RDSON	ID
30V	14mΩ	12A
-30V	23mΩ	-11.5A

Applications

- High Frequency Point-of-Load Synchronous Buck Converter for MB/NB/UMPC/VGA
- Networking DC-DC Power System
- CCFL Back-light Inverter

TO-252-4L Pin Configuration



Absolute Maximum Ratings

Symbol	Parameter	Rating		Units
		N-Ch	P-Ch	
V_{DS}	Drain-Source Voltage	30	-30	V
V_{GS}	Gate-Source Voltage	± 20	± 20	V
I_D	Continuous Drain Current, $V_{GS(NP)}=10V, T_a=25^\circ C$	12	-11.5	A
	Continuous Drain Current, $V_{GS(NP)}=10V, T_a=70^\circ C$	7.5	-9.6	A
I_{DP}^a	Pulse Drain Current Tested, $V_{GS(NP)}=10V$	48	-48	A
E_{AS}^c	Avalanche Energy, Single pulse, L=0.5mH	20	20	mJ
I_{AS}^c	Avalanche Current, Single pulse, L=0.5mH	9	-9	A
P_D	Total Power Dissipation, $T_a=25^\circ C$	5.25	5.25	W
T_{STG}	Storage Temperature Range	-55 to 175	-55 to 175	$^\circ C$
T_J	Operating Junction Temperature Range	175	175	$^\circ C$
$R_{\theta JA}^b$	Thermal Resistance-Junction to Ambient, Steady State	60	60	$^\circ C/W$
$R_{\theta JC}$	Thermal Resistance-Junction to Case, Steady State	6.25	6.25	$^\circ C/W$

Note * : Max. current is limited by bonding wire.

Note a : Pulse width limited by max. junction temperature.

Note b : $R_{\theta JA}$ steady state $t=999s$. $R_{\theta JA}$ is measured with the device mounted on $1in^2$, FR-4 board with 2oz. Copper.

Note c : UIS tested and pulse width limited by maximum junction temperature $175^\circ C$ (initial temperature $T_J=25^\circ C$).

N-Electrical Characteristics (T_J=25 °C, unless otherwise noted)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V, I _D =250uA	30	---	---	V
R _{DS(ON)} ^d	Static Drain-Source On-Resistance	V _{GS} =10V, I _D =8A	---	14	18.5	mΩ
		V _{GS} =4.5V, I _D =5A	---	17	25	
V _{GS(th)}	Gate Threshold Voltage	V _{GS} =V _{DS} , I _D =250uA	1.3	1.8	2.3	V
I _{DSS}	Drain-Source Leakage Current	V _{DS} =20V, V _{GS} =0V, T _J =25°C	---	---	1	uA
		V _{DS} =20V, V _{GS} =0V, T _J =85°C	---	---	30	
I _{GSS}	Gate-Source Leakage Current	V _{GS} =±20V, V _{DS} =0V	---	---	±100	nA
R _g	Gate Resistance	V _{DS} =0V, V _{GS} =0V, f=1MHz	---	1.7	3.4	Ω
Q _g ^e	Total Gate Charge	V _{DS} =15V, V _{GS} =4.5V, I _{DS} =8A	---	5.2	---	nC
Q _{gs} ^e	Gate-Source Charge		---	1.0	---	
Q _{gd} ^e	Gate-Drain Charge		---	2.8	---	
T _{d(on)} ^e	Turn-On Delay Time	V _{DD} =15V, R _L =15R, I _{DS} =1A, V _{GEN} =10V, R _G =6R.	---	6	---	ns
T _r ^e	Rise Time		---	8.6	---	
T _{d(off)} ^e	Turn-Off Delay Time		---	16	---	
T _f ^e	Fall Time		---	3.6	---	
C _{iss} ^e	Input Capacitance	V _{DS} =15V, V _{GS} =0V, f=1MHz	---	545	---	pF
C _{oss} ^e	Output Capacitance		---	95	---	
C _{rss} ^e	Reverse Transfer Capacitance		---	55	---	

Diode Characteristics

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
I _S	Continuous Source Current	V _G =V _D =0V, Force Current	---	---	12	A
V _{SD} ^d	Diode Forward Voltage	V _{GS} =0V, I _S =1A, T _J =25°C	---	---	1.2	V

Note d : Pulse test ; pulse width≤300μs, duty cycle≤2%.

Note e : Guaranteed by design, not subject to production testing.

P-Channel Electrical Characteristics ($T_J=25\text{ }^\circ\text{C}$, unless otherwise noted)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV_{DSS}	Drain-Source Breakdown Voltage	$V_{GS}=0V, I_D=-250\mu A$	-30	---	---	V
$R_{DS(ON)}^d$	Static Drain-Source On-Resistance	$V_{GS}=-10V, I_D=-12A$	---	23	32.5	m Ω
		$V_{GS}=-4.5V, I_D=-5A$	---	32	42	
$V_{GS(th)}$	Gate Threshold Voltage	$V_{GS}=V_{DS}, I_D=-250\mu A$	-1.3	-1.8	-2.3	V
I_{DSS}	Drain-Source Leakage Current	$V_{DS}=-20V, V_{GS}=0V, T_J=25^\circ\text{C}$	---	---	-1	μA
		$V_{DS}=-20V, V_{GS}=0V, T_J=85^\circ\text{C}$	---	---	-30	
I_{GSS}	Gate-Source Leakage Current	$V_{GS}=\pm 20V, V_{DS}=0V$	---	---	± 100	nA
Q_g^e	Total Gate Charge	$V_{DS}=-15V, V_{GS}=-4.5V, I_D=-12A$	---	13	---	nC
Q_{gs}^e	Gate-Source Charge		---	1.0	---	
Q_{gd}^e	Gate-Drain Charge		---	4.0	---	
$T_{d(on)}^e$	Turn-On Delay Time	$V_{DD}=-15V, V_{GS}=-10V, R_G=6\Omega, I_D=-1A, R_L=15\Omega,$	---	8.7	---	ns
T_r^e	Rise Time		---	10	---	
$T_{d(off)}^e$	Turn-Off Delay Time		---	22	---	
T_f^e	Fall Time		---	9.0	---	
C_{iss}^e	Input Capacitance	$V_{DS}=-15V, V_{GS}=0V, f=1\text{MHz}$	---	580	---	pF
C_{oss}^e	Output Capacitance		---	105	---	
C_{rss}^e	Reverse Transfer Capacitance		---	72	---	

Diode Characteristics

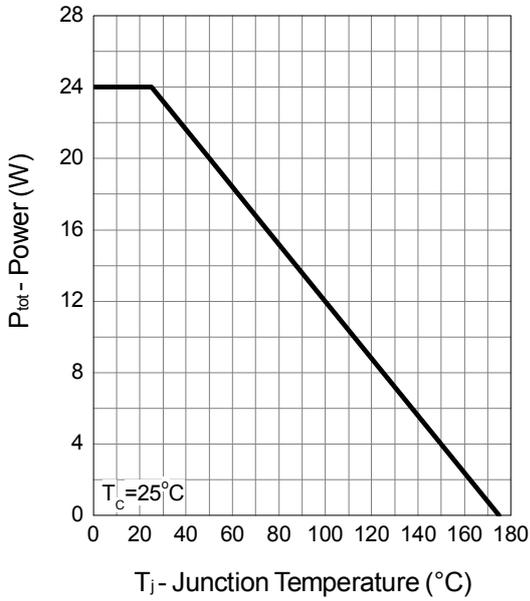
Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
I_S	Continuous Source Current	$V_G=V_D=0V$, Force Current	---	---	-10	A
V_{SD}^e	Diode Forward Voltage	$V_{GS}=0V, I_S=-1A, T_J=25^\circ\text{C}$	---	---	-1.2	V

Note d : Pulse test; pulse width $\leq 300\mu s$, duty cycle $\leq 2\%$.

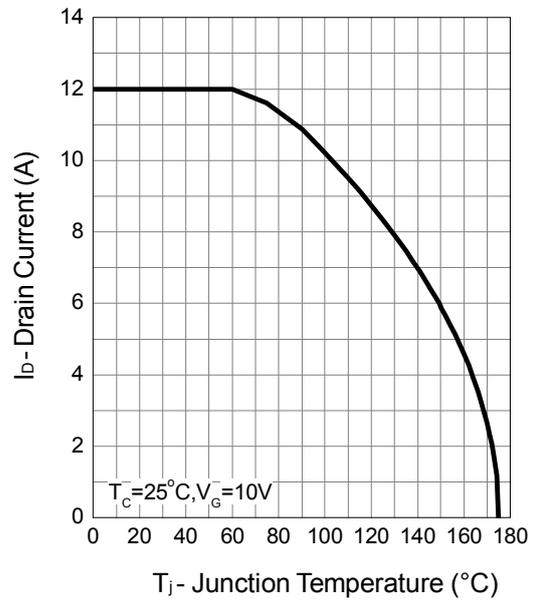
Note e : Guaranteed by design, not subject to production testing.

N-Channel Typical Characteristics

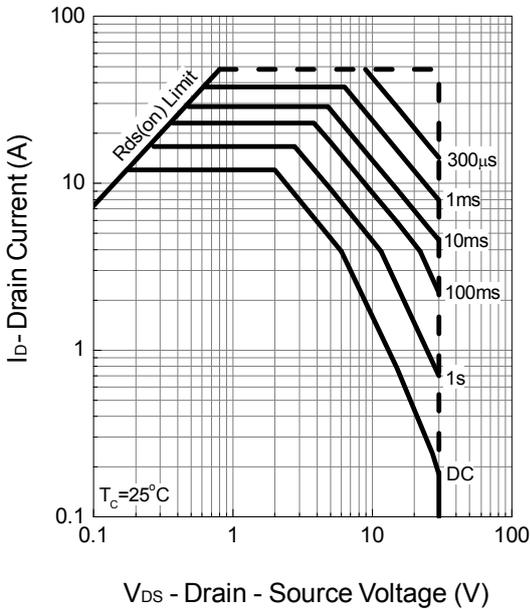
Power Dissipation



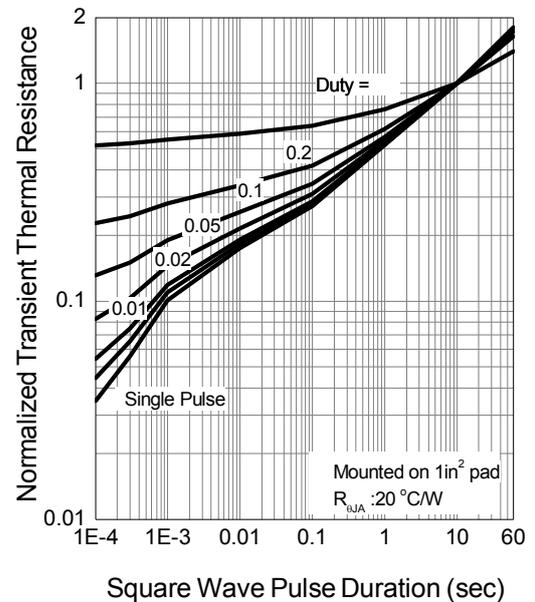
Drain Current



Safe Operation Area

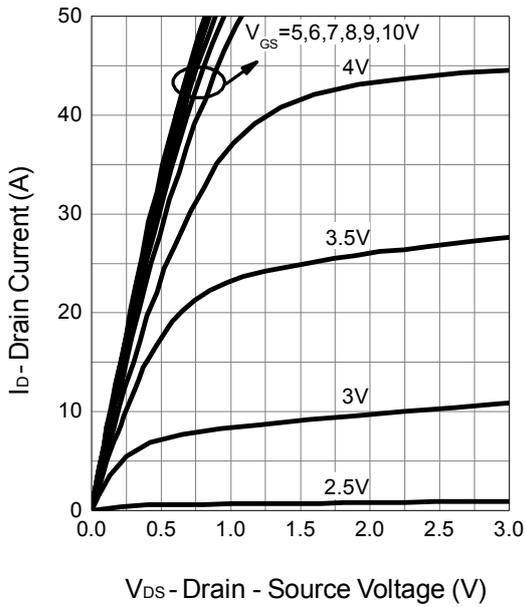


Thermal Transient Impedance

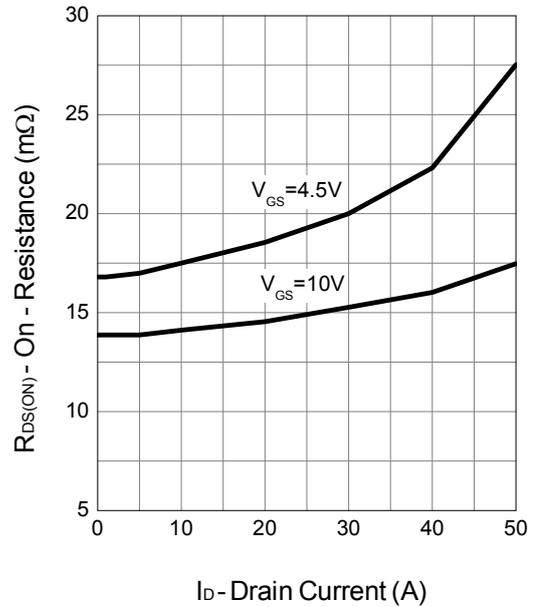


N-Channel Typical Characteristics

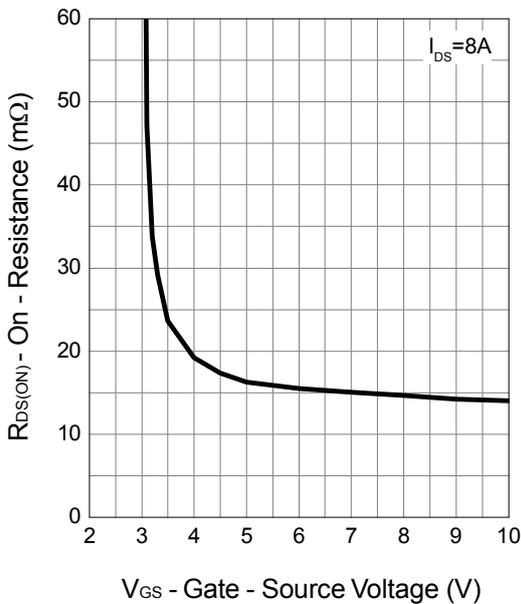
Output Characteristics



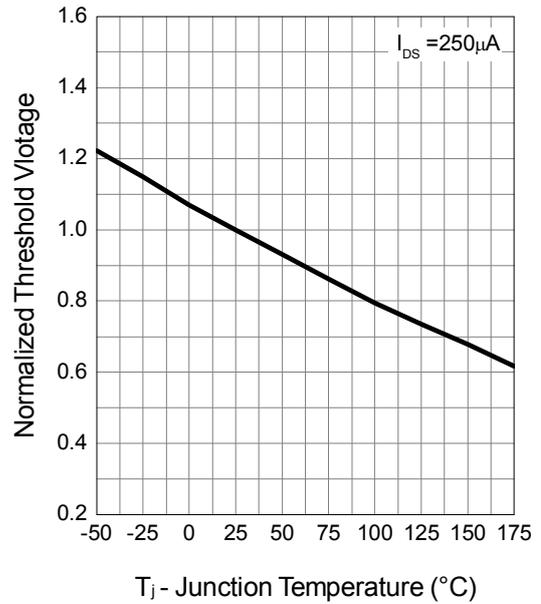
Drain-Source On Resistance



Gate-Source On Resistance

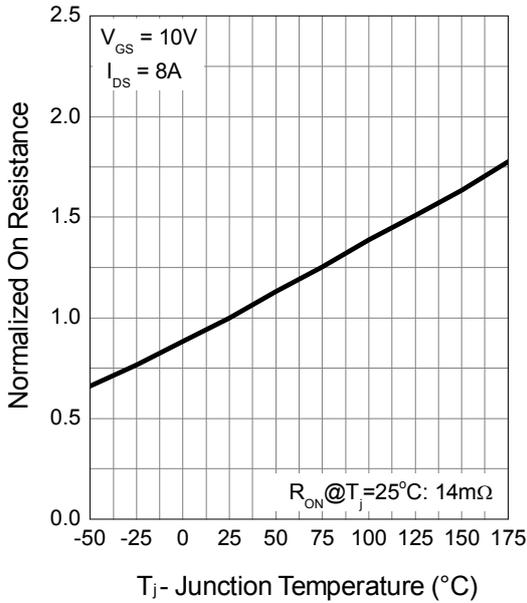


Gate Threshold Voltage

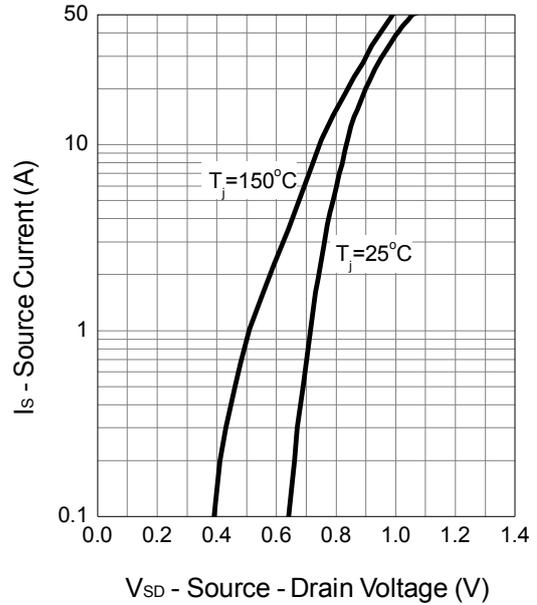


N-Channel Typical Characteristics

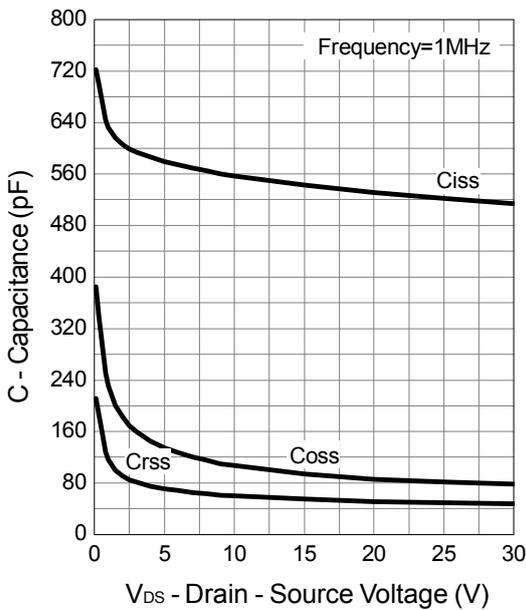
Drain-Source On Resistance



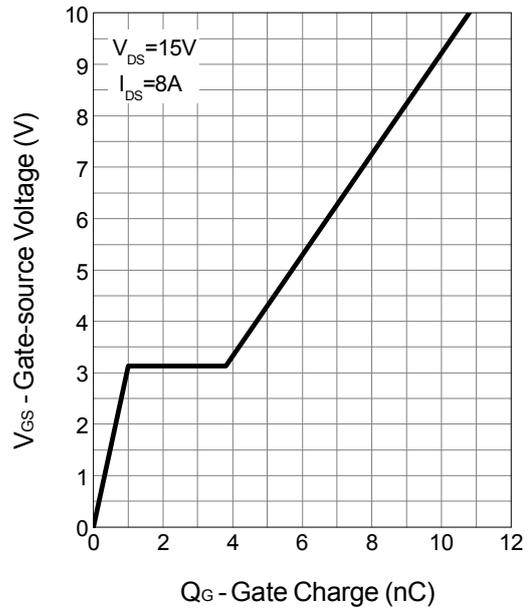
Source-Drain Diode Forward



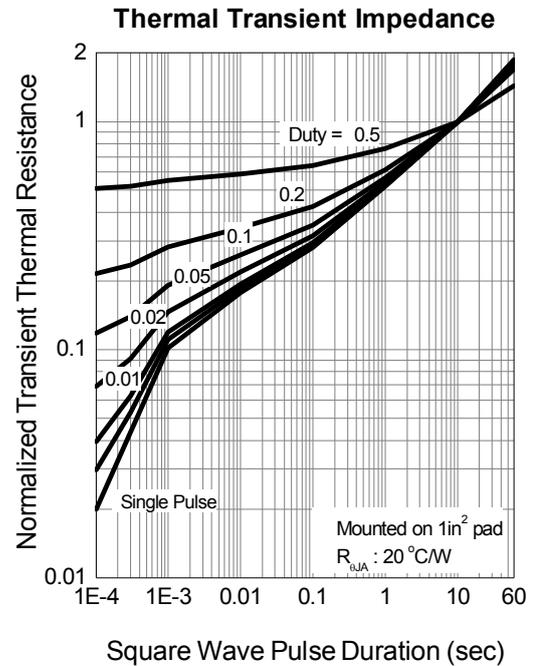
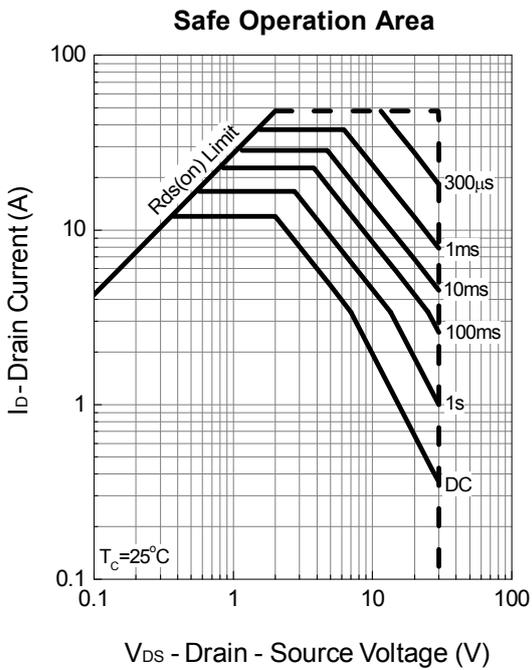
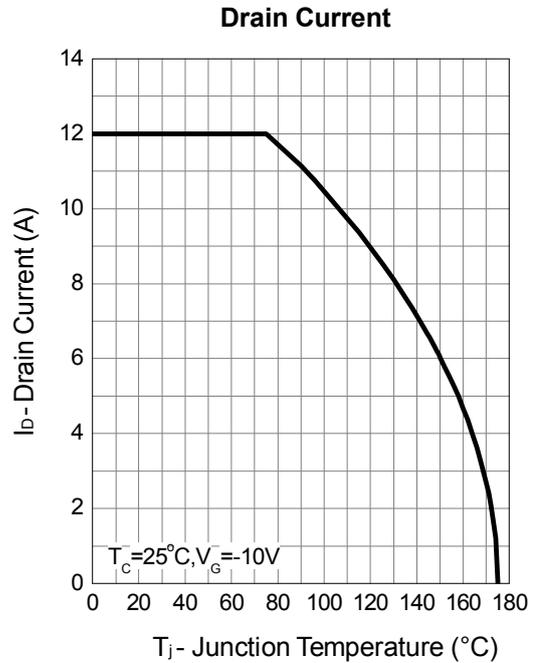
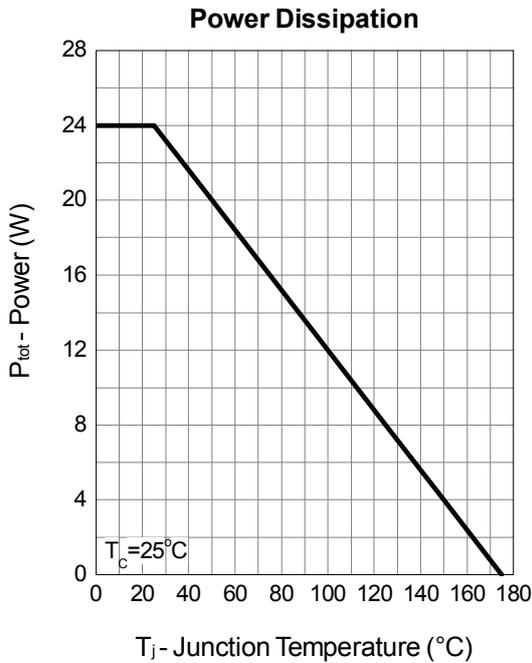
Capacitance



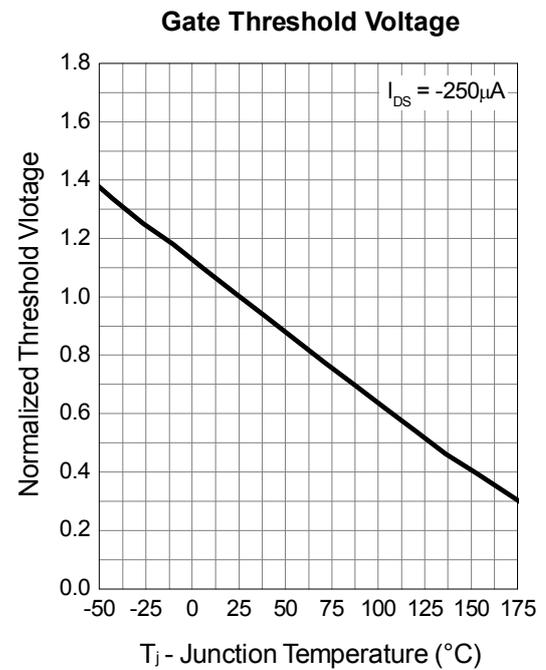
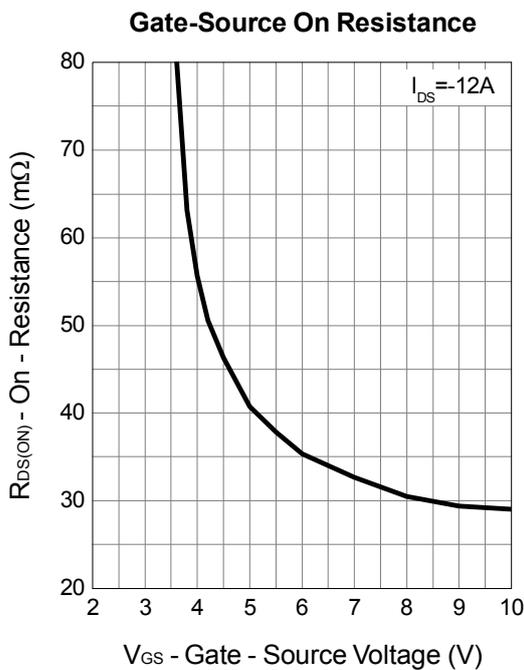
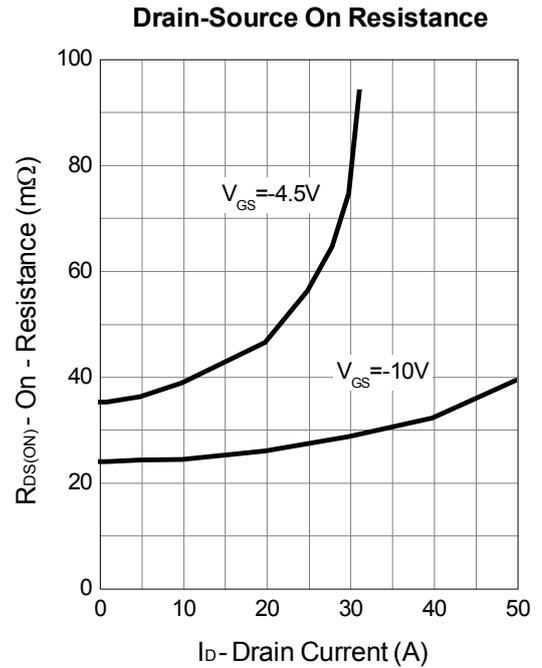
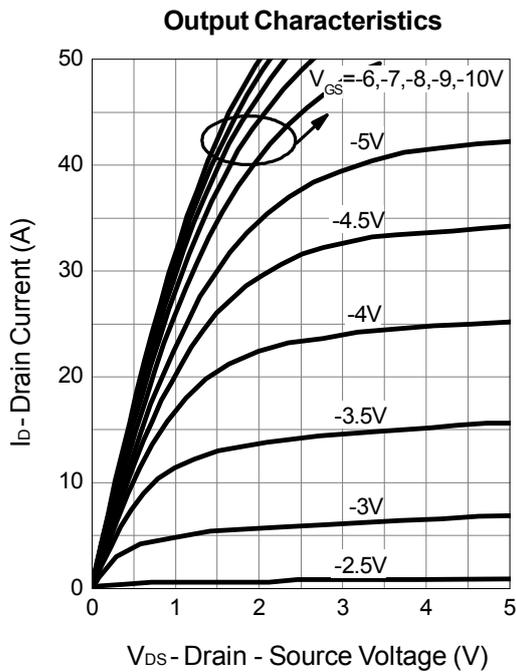
Gate Charge



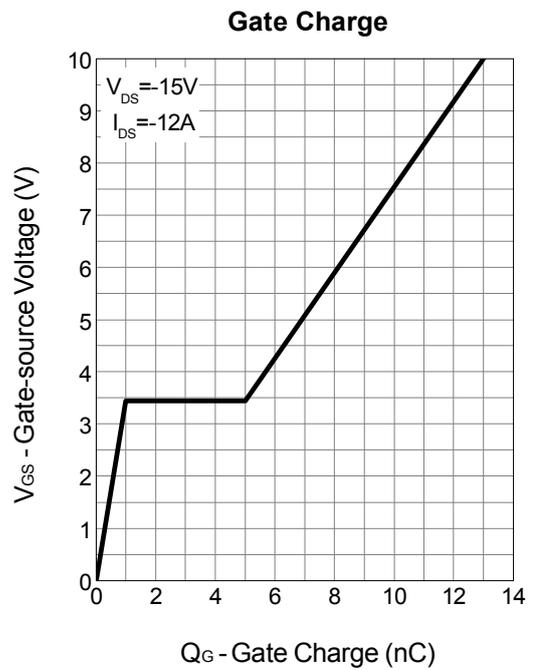
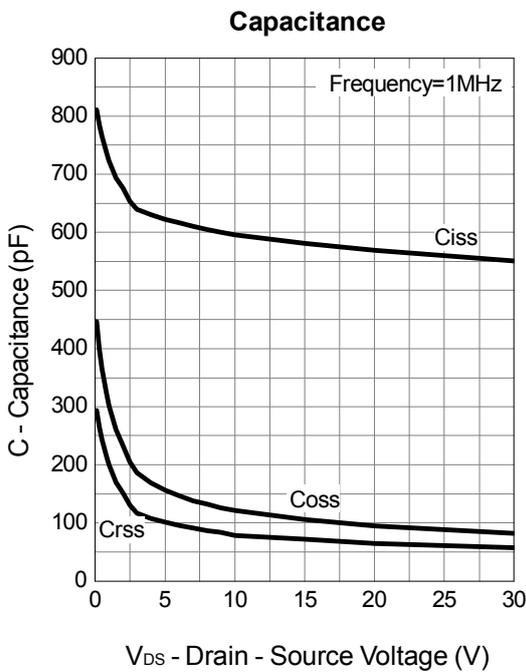
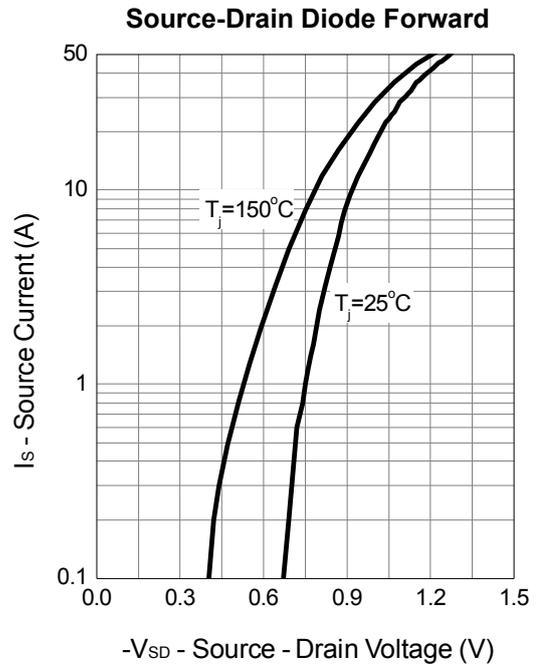
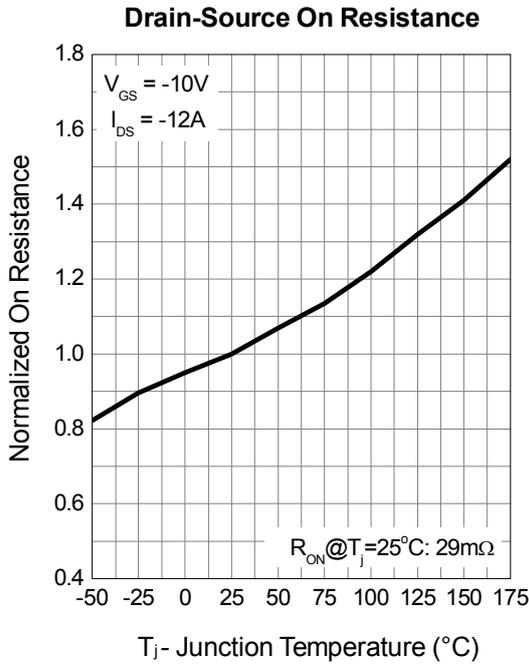
P-Channel Typical Characteristics

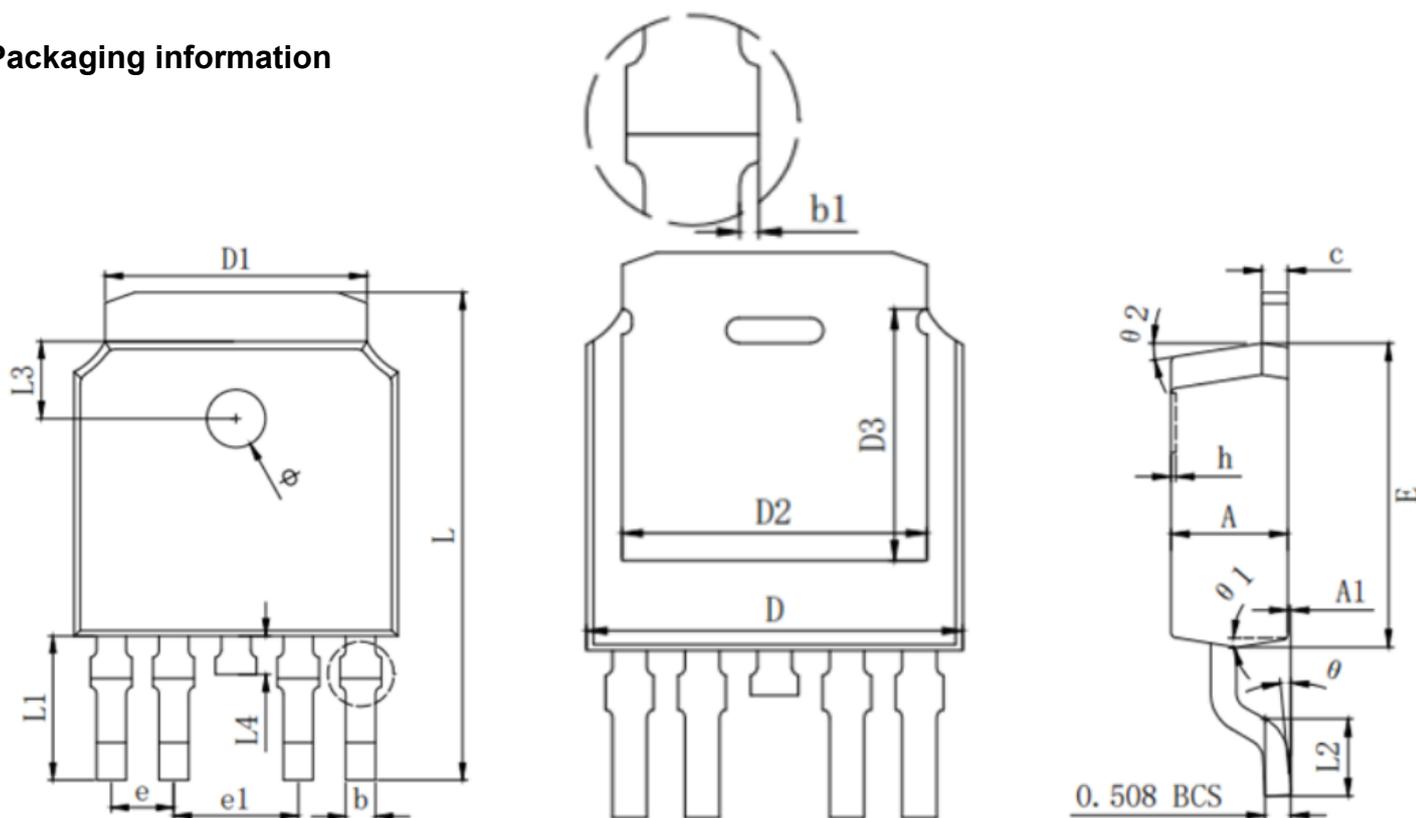


P-Channel Typical Characteristics



P-Channel Typical Characteristics



Packaging information


SYMBOLS	MILLIMETERS		
	MIN.	Typ.	MAX.
A	2.200	2.300	2.400
A1	0.000	-	0.127
b	0.550	0.600	0.650
b1	0.000	-	0.120
c(电镀后)	0.460	0.520	0.580
D	6.500	6.600	6.700
D1	5.334 REF		
D2	5.346 REF		
D3	4.490 REF		
E	6.000	6.100	6.200
e	1.270 TYP		
e1	2.540 TYP		
h	0.000	0.100	0.200
L	9.900	10.100	10.300
L1	2.988 REF		
L2	1.400	1.550	1.700
L3	1.600 REF		
L4	0.700	0.800	0.900
Φ	1.100	1.200	1.300
θ	0°	-	8°
θ 1	9° TYP		
θ 2	9° TYP		



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